

# 74HC1G86; 74HCT1G86

## 2-input EXCLUSIVE-OR gate

Rev. 04 — 20 July 2007

Product data sheet

### 1. General description

74HC1G86 and 74HCT1G86 are high-speed Si-gate CMOS devices. They provide a 2-input EXCLUSIVE-OR function.

The HC device has CMOS input switching levels and supply voltage range 2 V to 6 V.

The HCT device has TTL input switching levels and supply voltage range 4.5 V to 5.5 V.

The standard output currents are half those of the 74HC/HCT86.

### 2. Features

- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- SOT353-1 and SOT753 package options
- Specified from  $-40^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$

### 3. Ordering information

Table 1. Ordering information

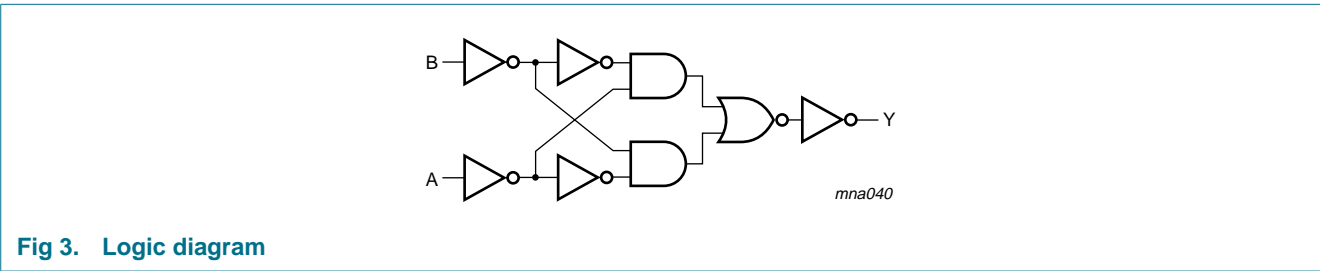
Type number	Package			
	Temperature range	Name	Description	Version
74HC1G86GW 74HCT1G86GW	$-40^{\circ}\text{C}$ to $+125^{\circ}\text{C}$	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1
74HC1G86GV 74HCT1G86GV	$-40^{\circ}\text{C}$ to $+125^{\circ}\text{C}$	SC-74A	plastic surface-mounted package; 5 leads	SOT753

### 4. Marking

Table 2. Marking codes

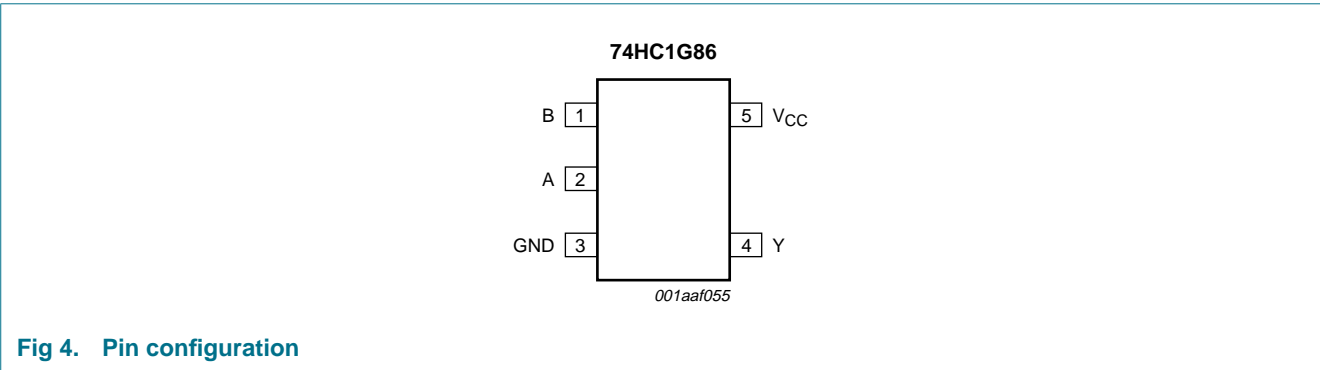
Type number	Marking
74HC1G86GW	HH
74HCT1G86GW	TH
74HC1G86GV	H86
74HCT1G86GV	T86

5. Functional diagram



6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
B	1	data input
A	2	data input
GND	3	ground (0 V)
Y	4	data output
V <sub>CC</sub>	5	supply voltage

## 7. Functional description

**Table 4. Function table**

H = HIGH voltage level; L = LOW voltage level

Inputs		Output
A	B	Y
L	L	L
L	H	H
H	L	H
H	H	L

## 8. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V). [\[1\]](#)

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		-0.5	+7.0	V
I <sub>IK</sub>	input clamping current	V <sub>I</sub> < -0.5 V or V <sub>I</sub> > V <sub>CC</sub> + 0.5 V	-	±20	mA
I <sub>OK</sub>	output clamping current	V <sub>O</sub> < -0.5 V or V <sub>O</sub> > V <sub>CC</sub> + 0.5 V	-	±20	mA
I <sub>O</sub>	output current	-0.5 V < V <sub>O</sub> < V <sub>CC</sub> + 0.5 V	-	±12.5	mA
I <sub>CC</sub>	supply current		-	25	mA
I <sub>GND</sub>	ground current		-25	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = -40 °C to +125 °C	<a href="#">[2]</a> -	200	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] Above 55 °C the value of P<sub>tot</sub> derates linearly with 2.5 mW/K.

## 9. Recommended operating conditions

**Table 6. Recommended operating conditions**

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74HC1G86			74HCT1G86			Unit
			Min	Typ	Max	Min	Typ	Max	
V <sub>CC</sub>	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V <sub>I</sub>	input voltage		0	-	V <sub>CC</sub>	0	-	V <sub>CC</sub>	V
V <sub>O</sub>	output voltage		0	-	V <sub>CC</sub>	0	-	V <sub>CC</sub>	V
T <sub>amb</sub>	ambient temperature		-40	+25	+125	-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	V <sub>CC</sub> = 2.0 V	-	-	625	-	-	-	ns/V
		V <sub>CC</sub> = 4.5 V	-	-	139	-	-	139	ns/V
		V <sub>CC</sub> = 6.0 V	-	-	83	-	-	-	ns/V

## 10. Static characteristics

**Table 7. Static characteristics**

Voltages are referenced to GND (ground = 0 V). All typical values are measured at  $T_{amb} = 25\text{ }^{\circ}\text{C}$ .

Symbol	Parameter	Conditions	−40 °C to +85 °C			−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	
For type 74HC1G86								
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 2.0 V	1.5	1.2	-	1.5	-	V
		V <sub>CC</sub> = 4.5 V	3.15	2.4	-	3.15	-	V
		V <sub>CC</sub> = 6.0 V	4.2	3.2	-	4.2	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 2.0 V	-	0.8	0.5	-	0.5	V
		V <sub>CC</sub> = 4.5 V	-	2.1	1.35	-	1.35	V
		V <sub>CC</sub> = 6.0 V	-	2.8	1.8	-	1.8	V
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>						
		I <sub>O</sub> = −20 μA; V <sub>CC</sub> = 2.0 V	1.9	2.0	-	1.9	-	V
		I <sub>O</sub> = −20 μA; V <sub>CC</sub> = 4.5 V	4.4	4.5	-	4.4	-	V
		I <sub>O</sub> = −20 μA; V <sub>CC</sub> = 6.0 V	5.9	6.0	-	5.9	-	V
		I <sub>O</sub> = −2.0 mA; V <sub>CC</sub> = 4.5 V	4.13	4.32	-	3.7	-	V
		I <sub>O</sub> = −2.6 mA; V <sub>CC</sub> = 6.0 V	5.63	5.81	-	5.2	-	V
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>						
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 2.0 V	-	0	0.1	-	0.1	V
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 4.5 V	-	0	0.1	-	0.1	V
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 6.0 V	-	0	0.1	-	0.1	V
		I <sub>O</sub> = 2.0 mA; V <sub>CC</sub> = 4.5 V	-	0.15	0.33	-	0.4	V
		I <sub>O</sub> = 2.6 mA; V <sub>CC</sub> = 6.0 V	-	0.16	0.33	-	0.4	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = V <sub>CC</sub> or GND; V <sub>CC</sub> = 6.0 V	-	-	1.0	-	1.0	μA
I <sub>CC</sub>	supply current	V <sub>I</sub> = V <sub>CC</sub> or GND; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 6.0 V	-	-	10	-	20	μA
C <sub>I</sub>	input capacitance		-	1.5	-	-	-	pF
For type 74HCT1G86								
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	V
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>						
		I <sub>O</sub> = −20 μA; V <sub>CC</sub> = 4.5 V	4.4	4.5	-	4.4	-	V
		I <sub>O</sub> = −2.0 mA; V <sub>CC</sub> = 4.5 V	4.13	4.32	-	3.7	-	V
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>						
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 4.5 V	-	0	0.1	-	0.1	V
		I <sub>O</sub> = 2.0 mA; V <sub>CC</sub> = 4.5 V	-	0.15	0.33	-	0.4	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = V <sub>CC</sub> or GND; V <sub>CC</sub> = 5.5 V	-	-	1.0	-	1.0	μA

**Table 7.** Static characteristics ...continued

Voltages are referenced to GND (ground = 0 V). All typical values are measured at  $T_{amb} = 25\text{ }^{\circ}\text{C}$ .

Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	
$I_{CC}$	supply current	$V_I = V_{CC}$ or GND; $I_O = 0\text{ A}$ ; $V_{CC} = 5.5\text{ V}$	-	-	10	-	20	$\mu\text{A}$
$\Delta I_{CC}$	additional supply current	per input; $V_{CC} = 4.5\text{ V}$ to $5.5\text{ V}$ ; $V_I = V_{CC} - 2.1\text{ V}$ ; $I_O = 0\text{ A}$	-	-	500	-	850	$\mu\text{A}$
$C_I$	input capacitance		-	1.5	-	-	-	pF

## 11. Dynamic characteristics

**Table 8.** Dynamic characteristics

$GND = 0\text{ V}$ ;  $t_r = t_f \leq 6.0\text{ ns}$ ; All typical values are measured at  $T_{amb} = 25\text{ }^{\circ}\text{C}$ . For test circuit see [Figure 6](#)

Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	

### For type 74HC1G86

$t_{pd}$	propagation delay	A and B to Y; see <a href="#">Figure 5</a>	<a href="#">[1]</a>					
		$V_{CC} = 2.0\text{ V}$ ; $C_L = 50\text{ pF}$	-	22	115	-	135	ns
		$V_{CC} = 4.5\text{ V}$ ; $C_L = 50\text{ pF}$	-	11	23	-	27	ns
		$V_{CC} = 5.0\text{ V}$ ; $C_L = 15\text{ pF}$	-	9	-	-	-	ns
		$V_{CC} = 6.0\text{ V}$ ; $C_L = 50\text{ pF}$	-	9	20	-	23	ns
$C_{PD}$	power dissipation capacitance	$V_I = GND$ to $V_{CC}$	<a href="#">[2]</a>					
			-	23	-	-	-	pF

### For type 74HCT1G86

$t_{pd}$	propagation delay	A and B to Y; see <a href="#">Figure 5</a>	<a href="#">[1]</a>					
		$V_{CC} = 4.5\text{ V}$ ; $C_L = 50\text{ pF}$	-	13	23	-	27	ns
		$V_{CC} = 5.0\text{ V}$ ; $C_L = 15\text{ pF}$	-	10	-	-	-	ns
$C_{PD}$	power dissipation capacitance	$V_I = GND$ to $V_{CC} - 1.5\text{ V}$	<a href="#">[2]</a>					
			-	23	-	-	-	pF

[1]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .

[2]  $C_{PD}$  is used to determine the dynamic power dissipation  $P_D$  ( $\mu\text{W}$ ).

$P_D = C_{PD} \times V_{CC}^2 \times f_i + \sum (C_L \times V_{CC}^2 \times f_o)$  where:

$f_i$  = input frequency in MHz

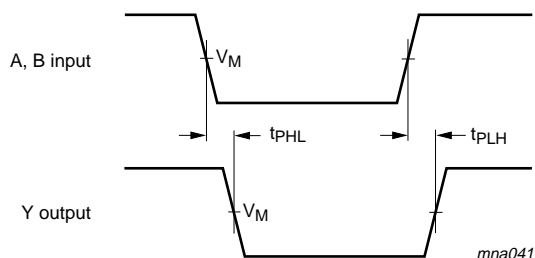
$f_o$  = output frequency in MHz

$C_L$  = output load capacitance in pF

$V_{CC}$  = supply voltage in Volts

$\sum (C_L \times V_{CC}^2 \times f_o)$  = sum of outputs

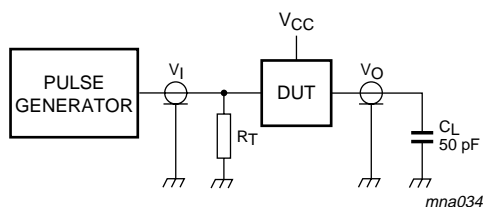
## 12. Waveforms



For 74HC1G86:  $V_M = 0.5 \times V_{CC}$ ;  $V_I = \text{GND to } V_{CC}$ .

For 74HCT1G86:  $V_M = 1.3 \text{ V}$ ;  $V_I = \text{GND to } 3.0 \text{ V}$ .

**Fig 5. The input (A and B) to output (Y) propagation delays**



Test data is given in [Table 8](#). Definitions for test circuit:

$C_L$  = Load capacitance including jig and probe capacitance.

$R_T$  = Termination resistance should be equal to output impedance  $Z_o$  of the pulse generator.

**Fig 6. Load circuitry for switching times**

13. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mmSOT353-1

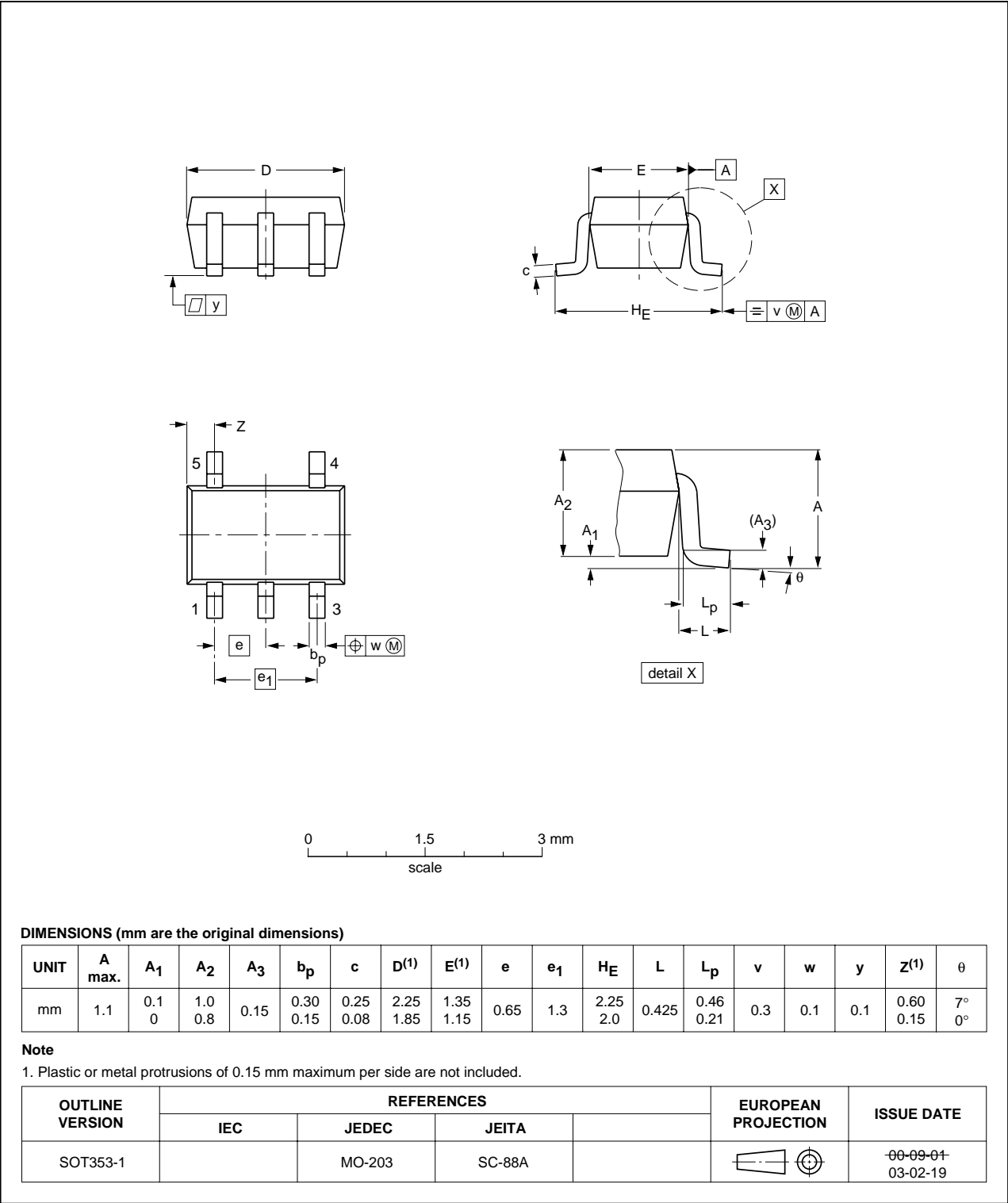


Fig 7. Package outline SOT353-1 (TSSOP5)

Plastic surface-mounted package; 5 leads

SOT753

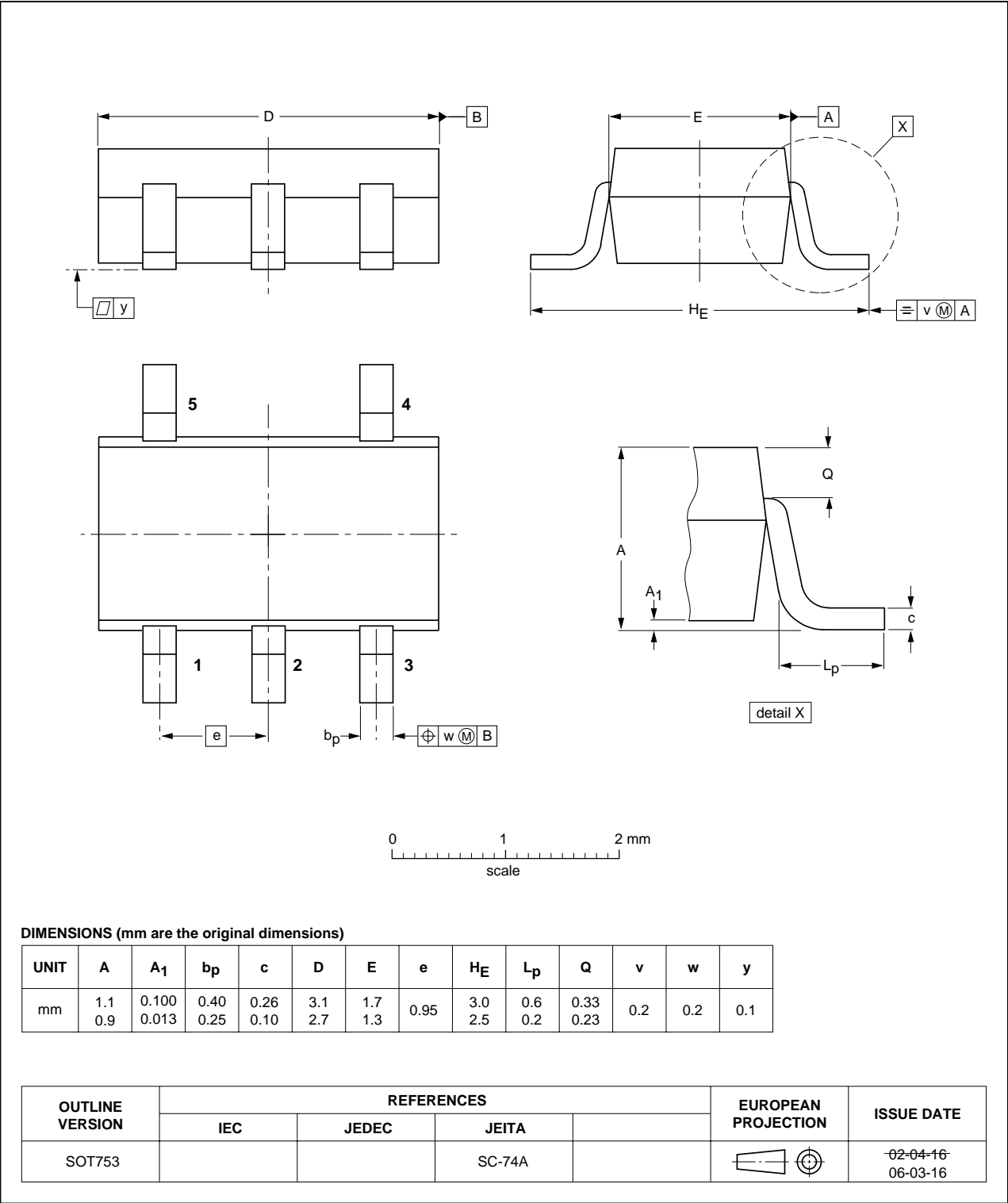


Fig 8. Package outline SOT753 (SC-74A)



## 14. Abbreviations

Table 9. Abbreviations

Acronym	Description
DUT	Device Under Test
TTL	Transistor-Transistor Logic

## 15. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT1G86_4	20070720	Product data sheet	-	74HC_HCT1G86_3
Modifications:	<ul style="list-style-type: none"><li>• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li><li>• Legal texts have been adapted to the new company name where appropriate.</li><li>• Package SOT353 changed to SOT353-1 in <a href="#">Table 1</a> and <a href="#">Figure 7</a>.</li><li>• Quick Reference Data and Soldering sections removed.</li><li>• <a href="#">Section 2 “Features”</a> updated.</li></ul>			
74HC_HCT1G86_3	20020515	Product specification	-	74HC_HCT1G86_2
74HC_HCT1G86_2	20010406	Product specification	-	74HC_HCT1G86_1
74HC_HCT1G86_1	19980805	Product specification	-	-

## 16. Legal information

### 16.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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[2] The term 'short data sheet' is explained in section "Definitions".

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